



**SMALL SIGNAL SCHOTTKY DIODE**

**VOLTAGE RANGE: 60 V**  
**POWER DISSIPATION:400 mW**

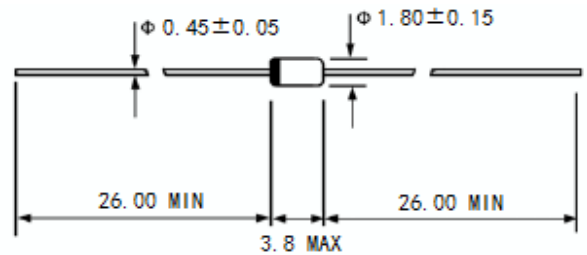
**FEATURES**

- ◇ For general purpose applications
- ◇ Metal silicon schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications

**MECHANICAL DATA**

- ◇ Case: JEDEC DO-35, glass case
- ◇ Polarity: Color band denotes cathode end
- ◇ Weight: Approx. 0.13 gram

**DO - 35(GLASS)**



Dimensions in millimeters

**ABSOLUTE RATINGS(LIMITING VALUES)**

	Symbols	Value	UNITS
Peak reverse voltage	$V_{RRM}$	60.0	V
Power dissipation (Infinite Heat Sink)	$P_{tot}$	400 <sup>1)</sup>	mW
Maximum single cycle surge 10 $\mu$ s square wave	$I_{FSM}$	2.0	A
Junction temperature	$T_J$	125	°C
Storage temperature range	$T_{STG}$	-55 ---+ 150	°C

1)Valid provided that electrodes are kept at ambient temperature.

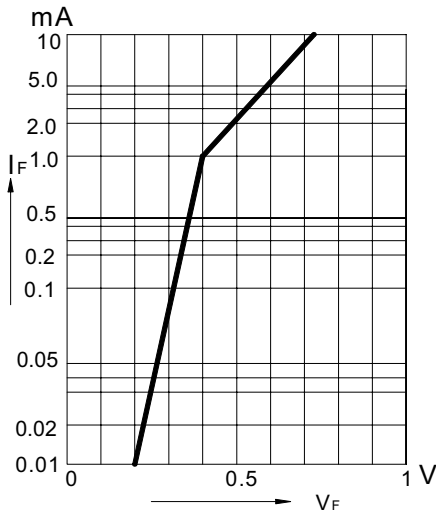
**ELECTRICAL CHARACTERISTICS**

(Ratings at 25°C ambient temperature unless otherwise specified)

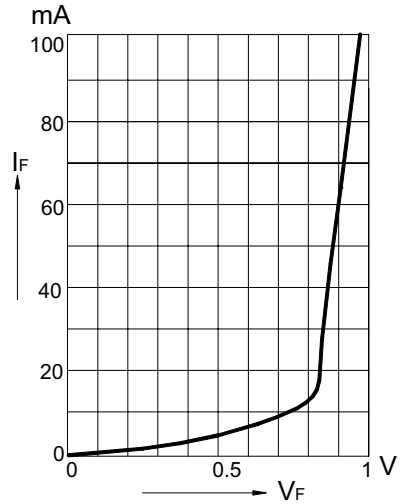
	Symbols	Min.	Typ.	Max.	UNITS
Reverse breakdown voltage @ $I_R=10\mu A$	$V_R$	60.0			V
Leakage current @ $V_R=50V$	$I_R$			200.0	nA
Forward voltage drop @ $I_F=1mA$ $I_F=15mA$	$V_F$			0.41	V
	$V_F$			1.0	V
Junction capacitance @ $V_R=0V, f=1MHz$	$C_J$			2.2	pF
Reverse recovery time @ $I_F=I_R=5mA, recover to 0.1 I_R$	$t_{rr}$			1	ns
Thermal resistance junction to ambient air	$R_{\theta JA}$			0.3	°C/mW

<sup>1)</sup> www.gmesemi.com

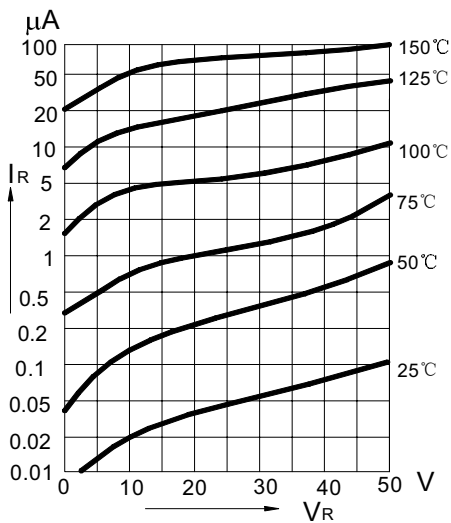
**FIG.1 – TYPICAL VARIATION OF FWD. CURRENT VS FWD. VOLTAGE FOR PRIMARY CONDUCTION THROUGH THE SCHOTTKY BARRIER**



**FIG.2 – TYPICAL FORWARD CONDUCTION CURVE OF COMBINATION SCHOTTKY BARRIER AND PN JUNCTION GUARD RING**



**FIG.3 – TYPICAL VARIATION OF REVERSE CURRENT AT VARIATION TEMPERATURES**



**FIG.4 – TYPICAL CAPACITANCE CURVE AS A FUNCTION OF REVERSE VOLTAGE**

